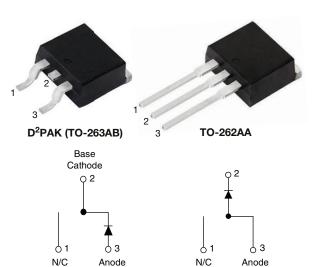
www.vishay.com

VS-15ETX06S-M3, VS-15ETX06-1-M3

Vishay Semiconductors

Hyperfast Rectifier, 15 A FRED Pt®



VS-15ETX06-1-M3

PRIMARY CHARACTERISTICS							
I _{F(AV)}	15 A						
V _R	600 V						
V _F at I _F	1.5 V						
t _{rr} (typ.)	18 ns						
T _J max.	175 °C						
Package	D ² PAK (TO-263AB), TO-262AA						
Circuit configuration	Single						

VS-15ETX06S-M3

FEATURES

- · Benchmark ultralow forward voltage drop
- Hyperfast recovery time
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Peak repetitive reverse voltage	V _{RRM}		600	V		
Average rectified forward current	I _{F(AV)}	T _C = 133 °C	15			
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	170	А		
Peak repetitive forward current	I _{FM}		30			
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-				
	N	I _F = 15 A	-	2.3	3.2	V			
Forward voltage	V _F	I _F = 15 A, T _J = 150 °C	-	1.5	1.8				
	I _R	$V_{R} = V_{R}$ rated	-	0.1	50				
Reverse leakage current		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	40	300	μA			
Junction capacitance	CT	V _R = 600 V	-	20	-	pF			
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH			

Revision: 21-Dec-2021

1

Document Number: 96302

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



FREE



www.vishay.com

Vishay Semiconductors

DYNAMIC RECOVERY CHA	RACTERI	STICS (T _C = 25 °C	unless otherwise s	pecified)			
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A}, \ dI_F/dt = 100$	A/μs, V _R = 30 V	-	18	22	
Poverse receiver time	+	$I_F = 15 \text{ A}, \text{ d}I_F/\text{d}t = 10$	0 Α/μs, V _R = 30 V	-	20	32	20
Reverse recovery time	t _{rr}	T _J = 25 °C		-	22	-	115
		T _J = 125 °C		-	52	-	
Pook receivery ourrent	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	2.4	-	•			
Peak recovery current		T _J = 125 °C		-	5.1	-	A
	0	T _J = 25 °C		-	TYP. MAX. UNITS 18 22		
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	150	-	nc
Reverse recovery time	t _{rr}		I _F = 15 A	-	37	-	ns
Peak recovery current	I _{RRM}	T _J = 125 °C	dI _F /dt = 800 A/µs	-	16	-	А
Reverse recovery charge	Q _{rr}		V _R = 390 V	-	350	-	nC

THERMAL - MECHANICAL	SPECIFIC	ATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to case per leg	R _{thJC}		-	1.0	1.3	
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-	
Maight			-	2.0	-	g
Weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking davias		Case style D ² PAK (TO-263AB)	15ETX06S			
Marking device		Case style TO-262AA		15ET	X06-1	



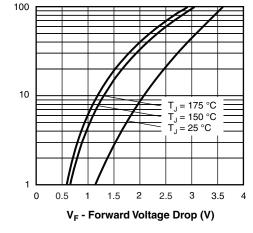
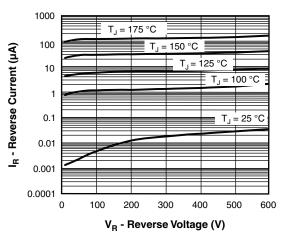


Fig. 1 - Typical Forward Voltage Drop Characteristics





Revision: 21-Dec-2021

2

Document Number: 96302

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



VS-15ETX06S-M3, VS-15ETX06-1-M3

Vishay Semiconductors

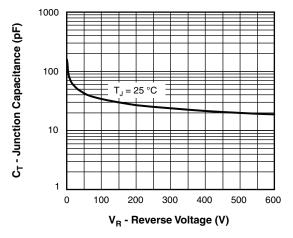


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

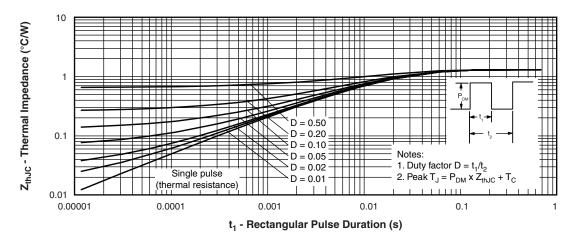


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

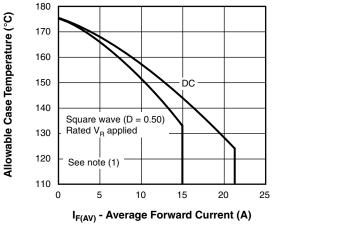


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

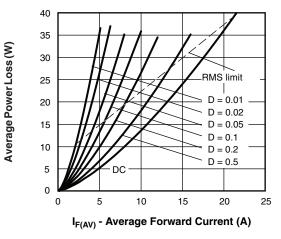


Fig. 6 - Forward Power Loss Characteristics

Revision: 21-Dec-2021

3

Document Number: 96302

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

VS-15ETX06S-M3, VS-15ETX06-1-M3



Vishay Semiconductors

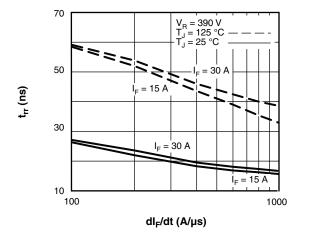


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

Note

- ⁽¹⁾ Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$;
 - Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at ($I_{F(AV)}/D$) (see fig. 6); Pd_{REV} = inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R

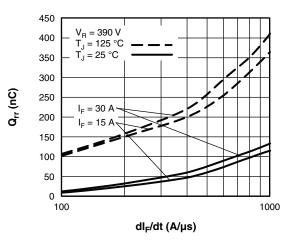


Fig. 8 - Typical Stored Charge vs. dl_F/dt

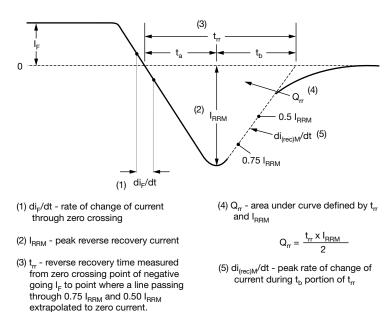
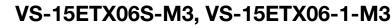


Fig. 9 - Reverse Recovery Waveform and Definitions



Vishay Semiconductors

ORDERING INFORMATION TABLE

www.vishay.com

SHAY

			_	_			_		
Device code	VS-	15	E	т	X	06	S	TRL	-M3
	1	2	3	4	5	6	7	8	9
	1 - 2 - 3 -	Cur	nay Sen rent rati single c	ng (15 A	-	oduct			
	4 -		TO-220		•	63AB)			
	5 - 6 -		hyperfa tage rati		-	1			
	7 -		= D ² PA						
		• -1	= TO-2	62AA					
	8 -	• N	one = tu	be (50 p	pieces)				
		• TI	RL = tap	e and re	eel (left	orientec	d, for D ²	² PAK (T	O-263A
	9 -		RR = tap ironmer			it oriente	ed, for l	D ² PAK ((TO-263
		-M3	= halog	en-free	, RoHS-	complia	nt, and	termina	tions le

ORDERING INFORMATION (Example)						
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-15ETX06S-M3	50	Antistatic plastic tubes				
VS-15ETX06STRR-M3	800	13" diameter plastic tape and reel				
VS-15ETX06STRL-M3	800	13" diameter plastic tape and reel				
VS-15ETX06-1-M3	50	Antistatic plastic tubes				

	LINKS TO RELAT	ED DOCUMENTS
Dimensions	D ² PAK (TO-263AB)	www.vishay.com/doc?96164
Dimensions	TO-262	www.vishay.com/doc?96165
Part marking information	D ² PAK (TO-263AB)	www.vishay.com/doc?95444
Fart marking information	TO-262	www.vishay.com/doc?95443
Packaging information		www.vishay.com/doc?96424

Document Number: 96302

Vishay Semiconductors

D²PAK

DIMENSIONS in millimeters and inches



ota	ted	90	°C
<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	MILLIM	MILLIMETERS		INCHES		
STMBOL	MIN.	MAX.	MIN. MAX.		NOTES	
А	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIM	ETERS	INCHES		NOTES	
	STWBOL	MIN.	MAX.	MIN.	MAX.	NOTES
	D1	6.86	8.00	0.270	0.315	3
	E	9.65	10.67	0.380	0.420	2, 3
	E1	7.90	8.80	0.311	0.346	3
	е	2.54	2.54 BSC		0.100 BSC	
	Н	14.61	15.88	0.575	0.625	
	L	1.78	2.79	0.070	0.110	
	L1	-	1.65	-	0.066	3
	L2	1.27	1.78	0.050	0.070	
	L3	0.25	BSC	0.010	BSC	
	L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

Revision: 13-Jul-17

1

Document Number: 96164

For technical questions within your region: DiodesAmericas@vishav.com, DiodesAsia@vishav.com, DiodesEurope@vishav.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishav.com/doc?91000



Outline Dimensions



Vishay Semiconductors

TO-262AA

DIMENSIONS in millimeters and inches





F D1 (3) (3) Section A - A Base (4) Plating b1. b3 metal ≰ c1 (4) -(b, b2)-Section B - B and C - C Scale: None





Diodes 1. - Anode (two die)/open (one die) 2., 4. - Cathode 3. - Anode

Lead assignments

CVMPOI	MILLIN	IETERS	INC	INCHES			
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		
А	4.06	4.83	0.160	0.190			
A1	2.03	3.02	0.080	0.119			
b	0.51	0.99	0.020	0.039			
b1	0.51	0.89	0.020	0.035	4		
b2	1.14	1.78	0.045	0.070			
b3	1.14	1.73	0.045	0.068	4		
С	0.38	0.74	0.015	0.029			
c1	0.38	0.58	0.015	0.023	4		
c2	1.14	1.65	0.045	0.065			
D	8.51	9.65	0.335	0.380	2		
D1	6.86	8.00	0.270	0.315	3		
E	9.65	10.67	0.380	0.420	2, 3		
E1	7.90	8.80	0.311	0.346	3		
е	2.54	BSC	0.100 BSC				
L	13.46	14.10	0.530	0.555			
L1	-	1.65	-	0.065	3		
L2	3.56	3.71	0.140	0.146			

 ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the second dimensioner of the second dimensis and the second dimensioner of the second dimensioner of the the outmost extremes of the plastic body (3)

Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only (5)

Controlling dimension: inches

(6) Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)

Revision: 30-Nov-17

1



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

© 2024 VISHAY INTERTECHNOLOGY, INC. ALL RIGHTS RESERVED

Revision: 01-Jul-2024